

AMENDMENTS TO THE SPECIFICATION

Page 6, paragraph 2:

However, these prior art substrate rotating ~~mechanism~~ mechanisms have the following drawbacks:

Page 7, paragraph 4:

(5) When the substrate rotating mechanism rotates the substrate by injecting a gas toward the reverse side of the substrate, a foreign object, such as a deposit caused by a part of reaction products, is subject to be whirled up at the substrate tray and its periphery by the injection of the gas, resulting in a deposit or adhesion of the foreign object at the reverse side and the front side of the substrate.

Page 15, paragraph 2:

Further, in the aforementioned film-forming device with a substrate rotating mechanism, the certain film-forming process may be a thin-film growth by Metal Organic Chemical Vapor Deposition (MOCVD) ~~(see FIG. 8)~~.